

Properties of a new series of Hamamatsu Si diodes

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A new series of diodes FZ-Si (Hamamatsu) investigated by: 1) a standar technique (I(V) and C(V)); 2) by microwave photoconductivity decay measurement; 3) the response on the linear front bias pulse technique (BELIV); 4) the photoconductivity specra in the extrinsic region. Measurements performed at room a tat low temperature. The results are compared with the similar measurements in other supplier and in irradiated samples.

Author: Prof. VAITKUS, Juozas (Vilnius University)

Co-authors: Mr VELICKA, Arunas (Vilnius University); Mr ULECKAS, Aurimas (Vilnius University); Dr GAUBAS, Eugenijus (Vilnius University); Mr KUSAKOVSKIJ, Jurij (Vilnius University); Mr ZILINSKAS, Kestutis (Vilnius University); Mr VAINORIUS, Neimantas (Vilnius University); Mr CEPONIS, Tomas (Vilnius University); Prof. KAZUKAUSKAS, Vaidotas (Vilnius University)

Presenter: Prof. VAITKUS, Juozas (Vilnius University)

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